



CST415 P-Ch 15V Fast Switching MOSFETs

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

CST415 Product Summary



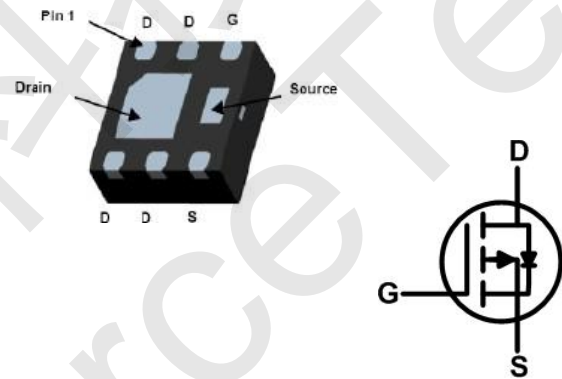
BVDSS	RDSON	ID
-15V	24mΩ	-7 A

CST415 Description

The CST415 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The CST415 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

CST415 DFN2020-6L Pin Configuration



CST415 Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-16	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current -Continuous	I_D	-7.0	A
Drain Current -Pulsed ^(Note 1)	I_{DM}	-15	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

CST415 Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	74	°C/W
---	-----------------	----	------



CST415 P-Ch 15V Fast Switching MOSFETs

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-16V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{DS}=V_{GS}, I_D=-250\mu A$	-15			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.45	-0.7	-1.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-4.1A$	-	24	45	m Ω
		$V_{GS}=-2.5V, I_D=-3A$	-	40	60	
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-4.1A$	5	-	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=-4V, V_{GS}=0V,$ $F=1.0MHz$	-	740	-	PF
Output Capacitance	C_{oss}		-	290	-	PF
Reverse Transfer Capacitance	C_{rss}		-	190	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-4V, I_D=-4.1A,$ $R_L=-1.2\Omega, V_{GEN}=-4.5V, R_g=1\Omega$	-	12	-	nS
Turn-on Rise Time	t_r		-	35	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	$V_{DS}=-4V, I_D=-4.1A, V_{GS}=-4.5V$	-	7.8	-	nC
Gate-Source Charge	Q_{gs}		-	1.2	-	nC
Gate-Drain Charge	Q_{gd}		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-4.1A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-7.1	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production



CST415 P-Ch 15V Fast Switching MOSFETs

CST415 Typical Electrical and Thermal Characteristics

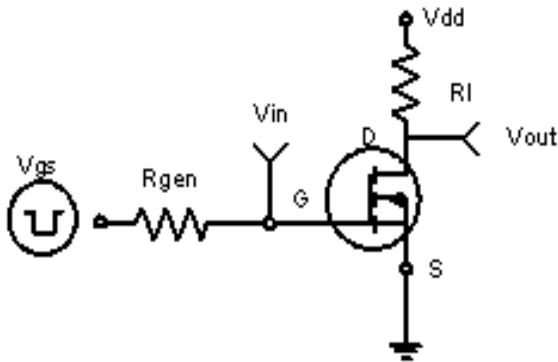


Figure 1: Switching Test Circuit

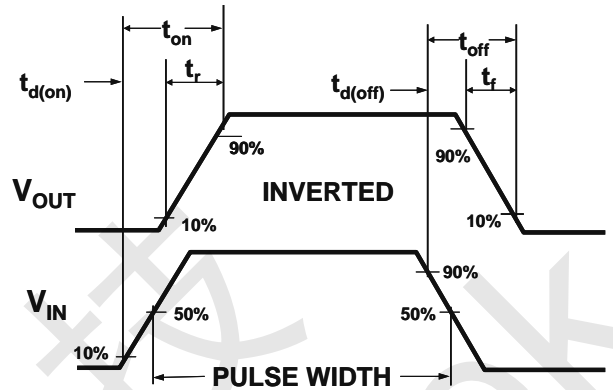


Figure 2: Switching Waveforms

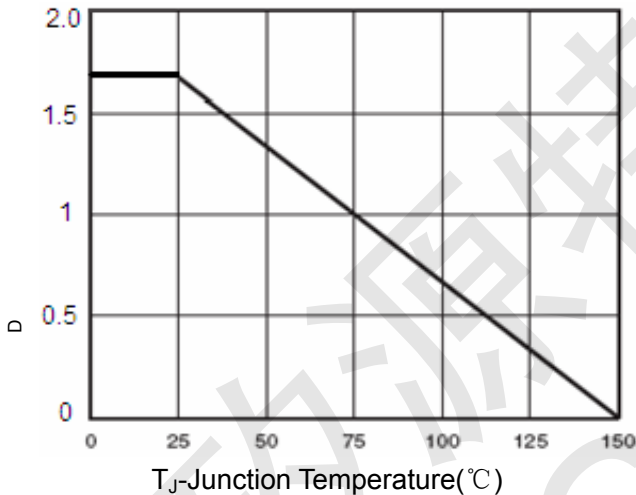


Figure 3 Power Dissipation

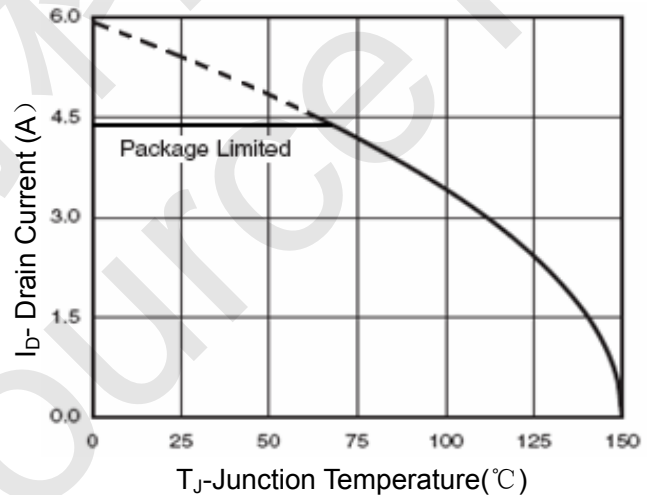


Figure 4 Drain Current

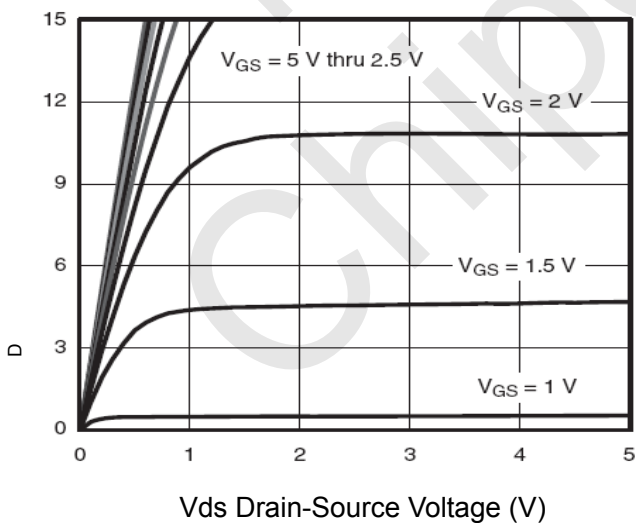


Figure 5 Output Characteristics

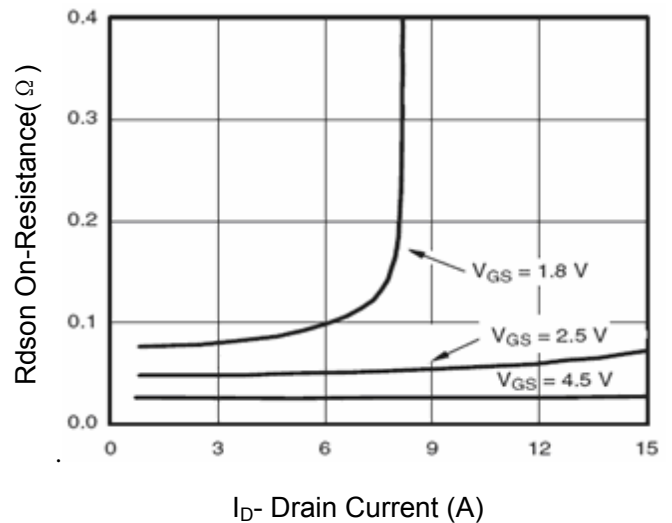


Figure 6 Drain-Source On-Resistance



CST415 P-Ch 15V Fast Switching MOSFETs

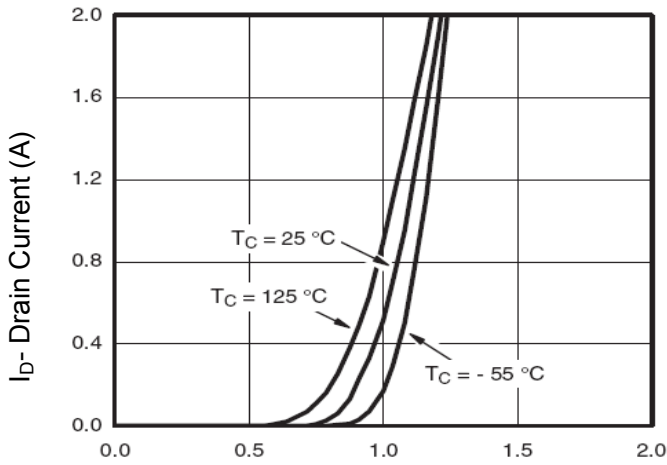


Figure 7 Transfer Characteristics

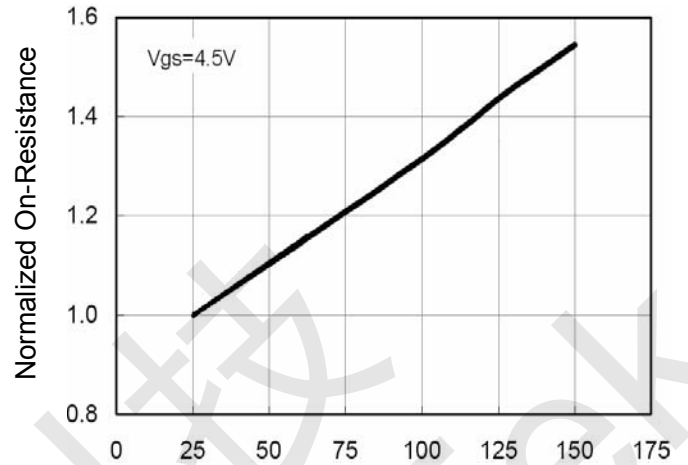


Figure 8 Drain-Source On-Resistance

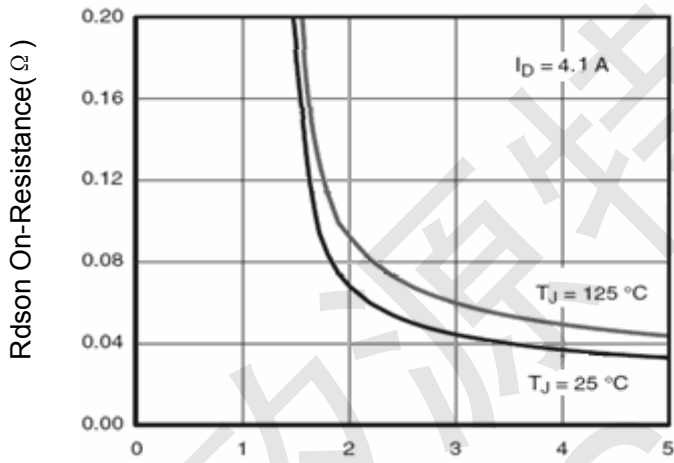


Figure 9 $R_{DS(on)}$ vs V_{GS}

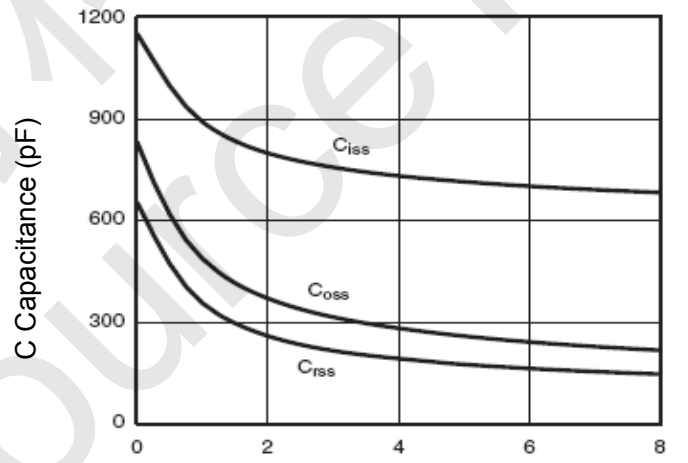


Figure 10 Capacitance vs V_{DS}

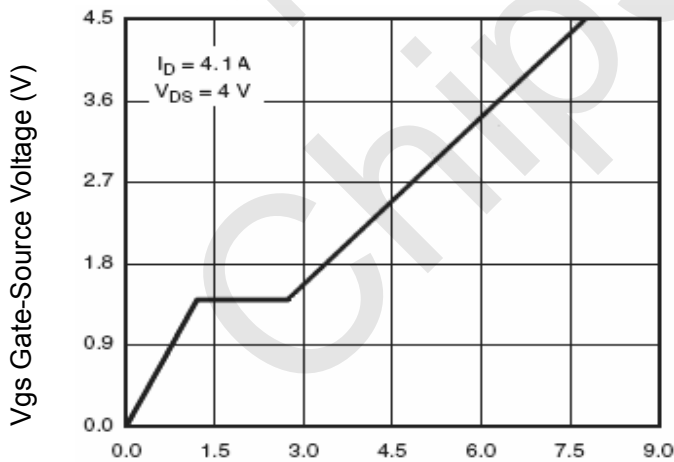


Figure 11 Gate Charge

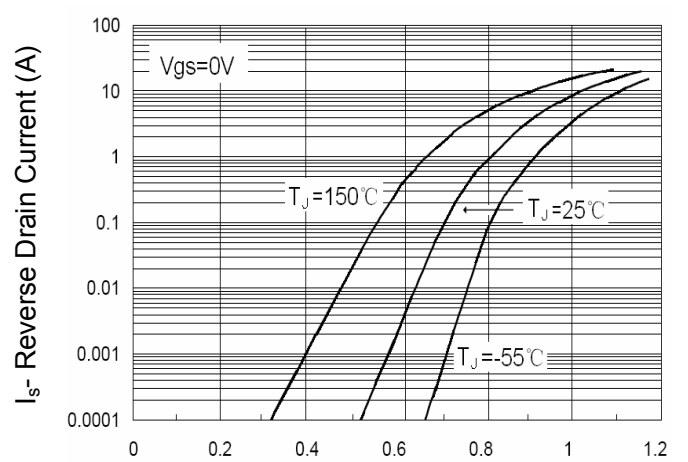
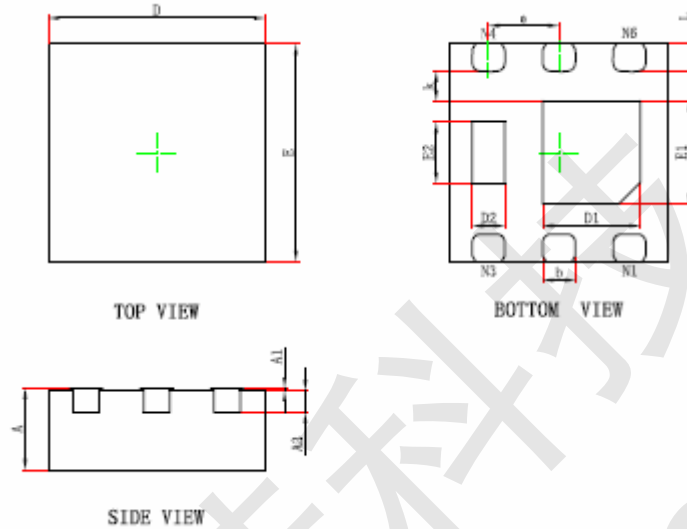


Figure 12 Source- Drain Diode Forward



CST415 DFN2020-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013